

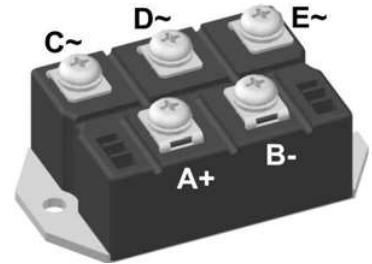
## Standard Rectifier Module


<b>3~ Rectifier</b>	
$V_{RRM}$	= 1400 V
$I_{DAV}$	= 125 A
$I_{FSM}$	= 1200 A

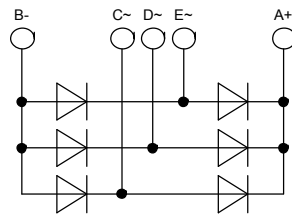
### 3~ Rectifier Bridge

Part number

VUO110-14N07



 E72873



#### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

#### Applications:

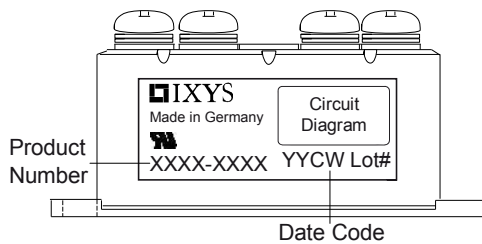
- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

#### Package: PWS-E

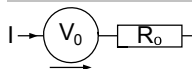
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}C$		1500	V
$V_{RRM}$	max. repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}C$		1400	V
$I_R$	reverse current	$V_R = 1400$ V		$T_{VJ} = 25^{\circ}C$		100	$\mu A$
		$V_R = 1400$ V		$T_{VJ} = 150^{\circ}C$		2	mA
$V_F$	forward voltage drop	$I_F = 50$ A		$T_{VJ} = 25^{\circ}C$		1.13	V
						1.46	V
		$I_F = 150$ A		$T_{VJ} = 125^{\circ}C$		1.04	V
						1.47	V
$I_{DAV}$	bridge output current	$T_C = 110^{\circ}C$		$T_{VJ} = 150^{\circ}C$		125	A
		rectangular	$d = 1/2$				
$V_{FO}$	threshold voltage			$T_{VJ} = 150^{\circ}C$		0.79	V
$r_F$	slope resistance						4.5
$R_{thJC}$	thermal resistance junction to case					0.7	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.3		K/W
$P_{tot}$	total power dissipation			$T_C = 25^{\circ}C$		175	W
$I_{FSM}$	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^{\circ}C$		1.20	kA
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		1.30	kA
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^{\circ}C$		1.02	kA
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		1.10	kA
$I^2t$	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^{\circ}C$		7.20	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		6.98	kA <sup>2</sup> s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^{\circ}C$		5.20	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		5.04	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^{\circ}C$		37	pF

Package PWS-E			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			200	A
$T_{stg}$	storage temperature		-40		125	°C
$T_{vj}$	virtual junction temperature		-40		150	°C
<b>Weight</b>				284		g
$M_D$	mounting torque		4.25		5.75	Nm
$M_T$	terminal torque		4.25		5.75	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	12.0			mm
$d_{Spb/App}$		terminal to backside	26.0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V

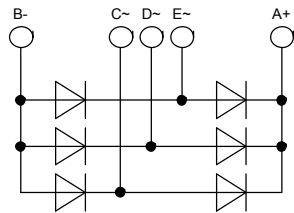
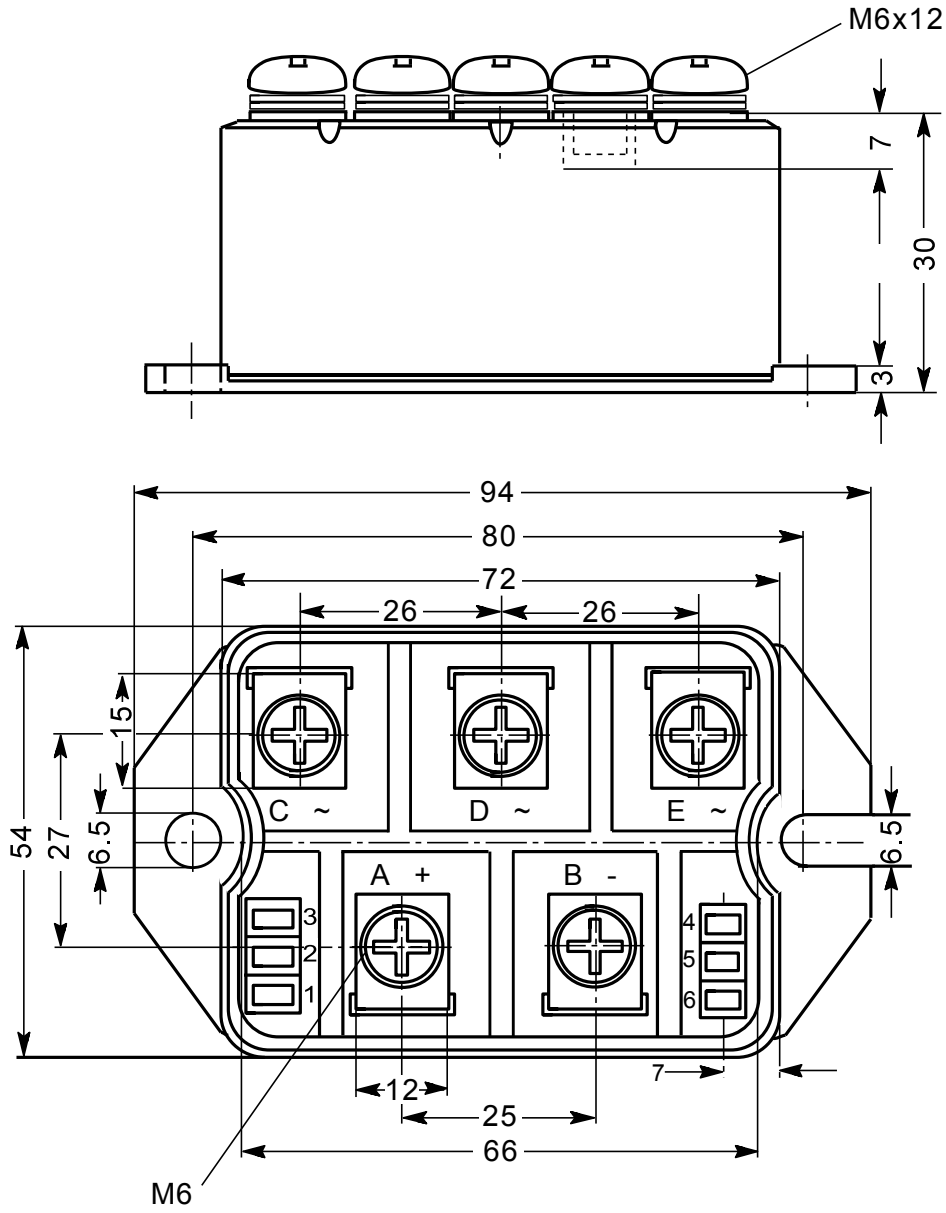


Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO110-14NO7	VUO110-14NO7	Box	5	462381

**Equivalent Circuits for Simulation**
*\* on die level*
 $T_{vj} = 150\text{ °C}$ 

**Rectifier**

$V_{0\max}$	threshold voltage	0.79	V
$R_{0\max}$	slope resistance *	3.3	mΩ

**Outlines PWS-E**



Rectifier

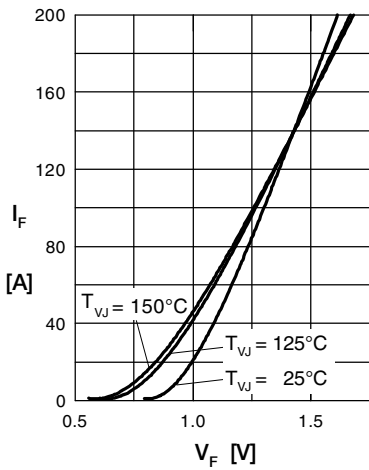


Fig. 1 Forward current vs. voltage drop per diode

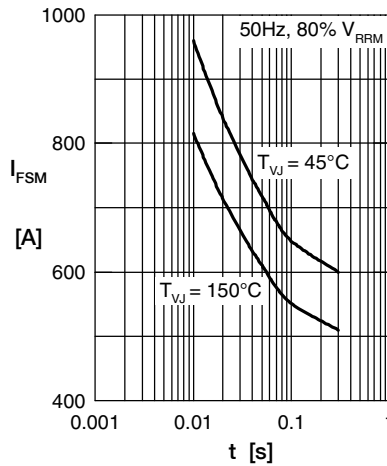


Fig. 2 Surge overload current vs. time per diode

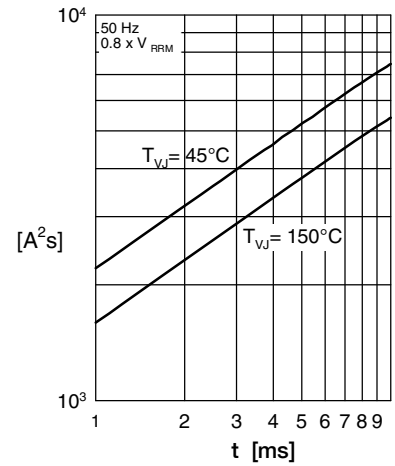


Fig. 3  $I^2t$  vs. time per diode

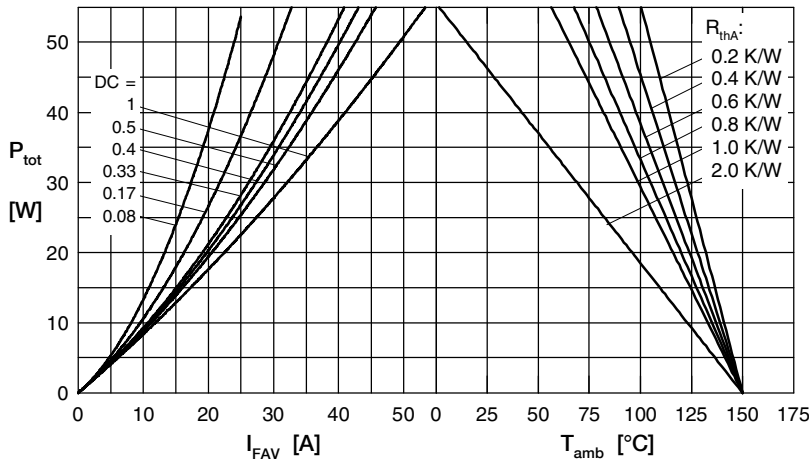


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

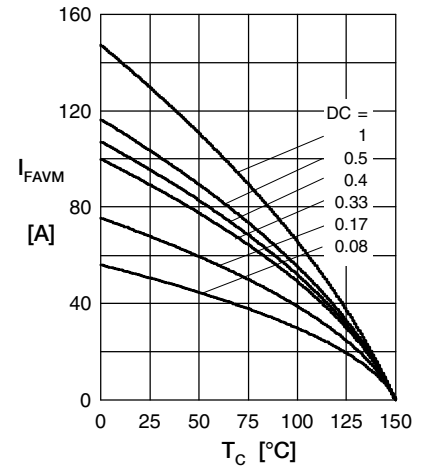


Fig. 5 Max. forward current vs. case temperature per diode

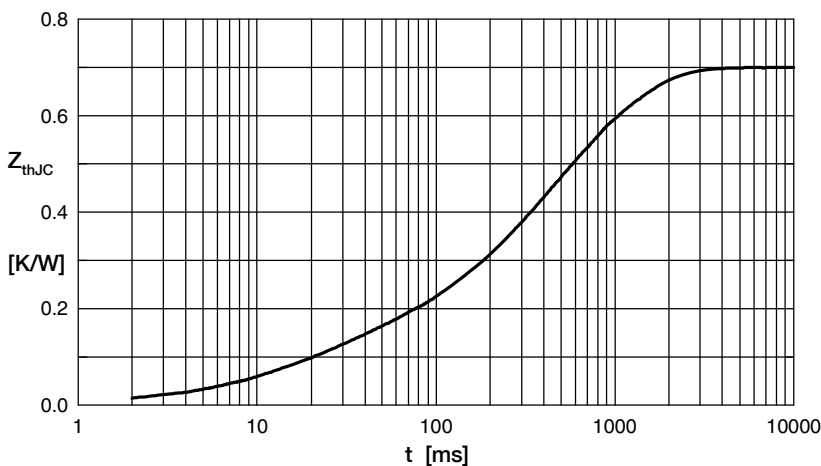


Fig. 6 Transient thermal impedance junction to case vs. time per diode

$R_i$	$t_i$
0.100	0.020
0.010	0.010
0.162	0.225
0.258	0.800
0.170	0.580